TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# 2SK1529

#### **High-Power Amplifier Application**

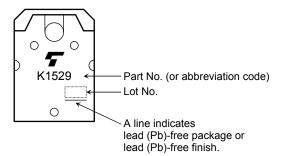
- High breakdown voltage  $: V_{DSS} = 180V$
- High forward transfer admittance  $|Y_{fs}| = 4.0 \text{ S (typ.)}$
- Complementary to 2SJ200

### Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage	V <sub>DSS</sub>	180	V	
Gate-source voltage	V <sub>GSS</sub>	±20	V	
Drain current (Note 1)	۱ <sub>D</sub>	10	А	
Drain power dissipation (Tc = 25°C)	PD	120	W	
Channel temperature	Тc	150	°C	
Storage temperature range	T <sub>stg</sub>	-55~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### Marking



Weight: 4.6 g (typ.)

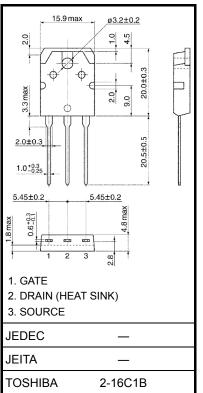
### Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 180 V, V <sub>GS</sub> = 0	_	_	1.0	mA
Gate leakage current	I <sub>GSS</sub>	V <sub>DS</sub> = 0, V <sub>GS</sub> = ±20 V	_	_	±0.5	μA
Drain-source breakdown voltage	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0	180	—	—	V
Drain-source saturation voltage	V <sub>DS (ON)</sub>	I <sub>D</sub> = 6 A, V <sub>GS</sub> = 10 V	_	2.5	5.0	V
Gate-source cut-off voltage (Note 2)	V <sub>GS (OFF)</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.1 A	0.8	—	2.8	V
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3 A	—	4.0	—	S
Input capacitance	C <sub>iss</sub>	$V_{DS}$ = 30 V, $V_{GS}$ = 0, f = 1 MHz	_	700	_	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0, f = 1 MHz	—	150	—	pF
Reverse transfer capacitance	C <sub>rss</sub>	V <sub>DD</sub> = 30 V, V <sub>GS</sub> = 0, f = 1 MHz	—	90	_	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: VGS (OFF) Classification 0: 0.8~1.6 Y: 1.4~2.8

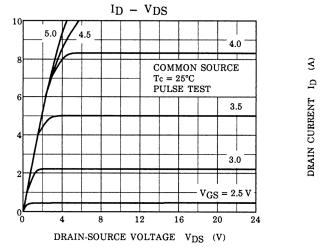
This transistor is an electrostatic-sensitive device. Please handle with caution.

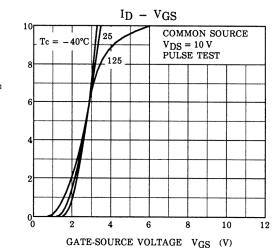


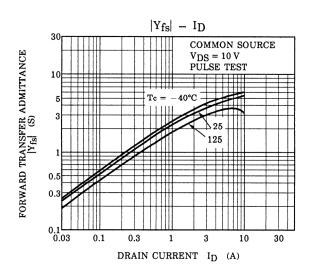
Unit: mm

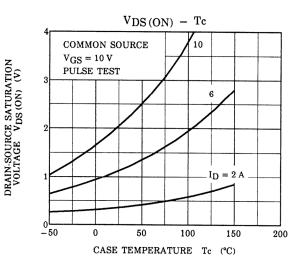
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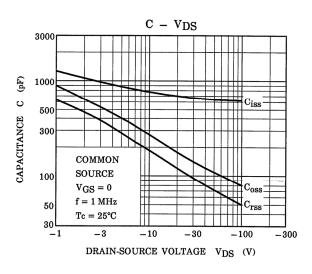


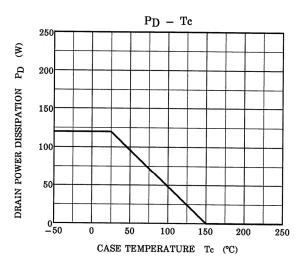




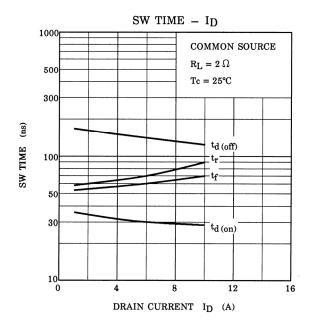


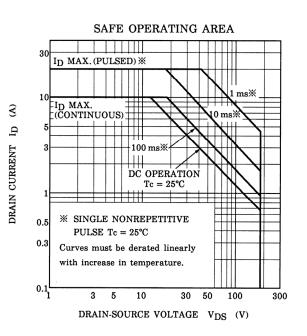




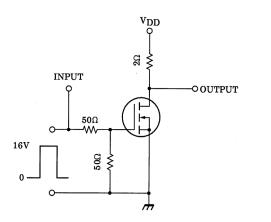


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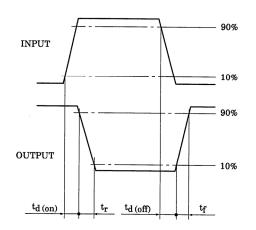




### **Switching Time Test Circuit**



### Waveforms



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